Table of Contents

1. FORMATION OF A CHEMICAL COMPOUND LAYER AT THE INTERFACE OF TWO ELEMENTARY SUBSTANCES 1

1.1 Description of the kinetics of solid-state heterogeneous reactions 1

1.2 Reaction diffusion 3

1.3 Growth of the A_pB_q layer at the expense of diffusion of component B 7

1.3.1 Critical thickness of the A_pB_q layer with regard to component B 13

1.3.2 Growth regime of the A_pB_q layer with regard to component B: theoretical definition 16

1.3.3 Stationary point 17

1.4 Growth of the A_pB_q layer at the expense of diffusion of components A and B 19

1.4.1 Critical thickness and growth regime of the A_pB_q layer with regard to component A 21

1.4.2 One compound layer: general kinetic equation 23

1.4.3 Separate determination of reaction-diffusion constants 28

1.5 Linear growth of the Cu_6Sn_5 layer in the copper-tin reaction couple 31

1.6 Parabolic growth of the AlSb layer in the aluminium-antimony diffusion couple 34

1.7 Linear-parabolic growth of the SiO_2 layer between silicon and oxygen 38

1.8 Growth kinetics of the $NiBi_3$ layer at the nickel-bismuth interface 41

1.8.1 Experimental details 42

1.8.2 Intermetallic layer composition 43

1.8.3 The main diffusing component during growth of the $NiBi_3$ layer 45

1.8.4 $NiBi_3$ layer growth kinetics 49

1.9 Interconnection between the reaction- and self-diffusion coefficient of the components of a chemical compound 52

1.10 Single compound layer: short conclusions 68

2. GROWTH KINETICS OF TWO COMPOUND LAYERS BETWEEN ELEMENTARY SUBSTANCES 69

2.1 Partial chemical reactions at phase interfaces 70

2.2 A system of differential equations describing the rates of formation of two chemical compound layers 73

2.3 Initial linear growth of the A_pB_q and A_rB_s layers 80

2.4 Minimal thickness of the A_rB_s layer necessary for the A_PB_Q layer to occur 84
2.5 Non-linear growth of the A_PB_q layer 86
2.6 Effect of the critical thickness of the A_PB_q layer with regard to component A on the process of growth of the A_rB_s layer 88
2.7 Paralinear growth kinetics of two compound layers 90
2.8 Diffusion controlled growth of the A_PB_q and A_rB_s layers 96
2.8.1 Late diffusional stage of formation of two compound layers: system of differential equations 98
2.8.2 Late diffusional stage of formation of two compound layers: ratio of their thickness 99
2.8.3 Simultaneous diffusional growth of the Al_3Mg_2 and $Al_{12}Mg_{17}$ intermetallic layers between aluminum and magnesium 106
2.9 NiBi layer: missing or too thin? 112
2.10 Two compound layers: short conclusions 114

3. OCCURRENCE OF MULTIPLE COMPOUND LAYERS AT THE *A–B* INTERFACE 117

3.1 Chemical reactions at phase interfaces in a multiphase binary system 120
3.2 A system of differential equations describing the growth process of three chemical compound layers between elementary substances A and B 122
3.3 Initial linear growth of three compound layers 126
3.4 Transition from linear to non-linear layer-growth kinetics 128
3.5 Critical values of compound-layer thicknesses and their influence on layer-growth kinetics 130
3.6 Diffusional stage of formation of compound layers 132
3.7 Sequence of compound-layer formation at the A–B interface 135
3.7.1 Phase-diagram predictions 135
3.7.2 Thermodynamic predictions 140
3.7.3 Reasons for the formation of multiple compound layers at the A–B interface 145
3.8 Formation of intermetallic layers in Ni–Zn and Co–Zn diffusion couples 152
3.8.1 Ni–Zn and Co–Zn phase diagrams 153
3.8.2 Materials, specimen preparation and experimental methods 153
3.8.3 Layer identification 156

3.8.4 Chemical composition of intermetallic layers 159
3.8.5 Layer-growth kinetics 165
3.9 Multiple compound layers: short conclusions 171

4. GROWTH KINETICS OF THE SAME CHEMICAL COMPOUND LAYER IN VARIOUS REACTION COUPLES OF A MULTIPHASE BINARY SYSTEM 173
4.1. Growth of the A_rB_s layer in the A–B reaction couple 173
4.2 Growth of the A_rB_s layer in the A_PB_q–B reaction couple 174
4.2.1 Growth of the A_rB_s layer between A_PB_q and B at the expense of diffusion of component A 175
4.2.2 Growth of the A_rB_s layer between A_PB_q and B at the expense of diffusion of both components 178
4.3 Growth of the A_rB_s layer in the A_PB_q –A_lB_n reaction couple 181
4.4 Comparison of the growth rates of the A_rB_s layer in various reaction couples of the A–B multiphase binary system 183
4.5 Duplex structure of the A_rB_s layer 194
4.6 Growth of the chemical compound layer in various reaction couples: short conclusions 201

5. REACTION-DIFFUSION KINETICS IN SOLID-LIQUID AND SOLID-GAS SYSTEMS 203
5.1 Main relationships governing dissolution of solids in liquids 203
5.2 Experimental investigation of the dissolution process of a solid in a liquid 208
5.2.1 Determination of the saturation concentration 211
5.2.2 Evaluation of the dissolution-rate constant 217
5.2.3 Estimation of the diffusion coefficient 221
5.3 Growth kinetics of the chemical compound layer under conditions of its simultaneous dissolution in the liquid phase 223
5.4 Growth kinetics of intermetallic layers at the transition metal-liquid aluminum interface 232
5.4.1 Formation of the Fe_2Al_5 layer between Fe and Al 232
5.4.2 Occurrence of the $MoAl_4$ layer between Mo and Al 235
5.4.3 Formation of intermetallics between Fe–Ni and Fe–Cr alloys and liquid aluminum 237
5.5 Interfacial interaction of nickel and cobalt with liquid Pb-free soldering alloys 251
5.5.1 Interaction of solid nickel with liquid bismuth and bismuth-based alloys 251

5.5.2 Interaction of solid nickel with liquid Sn–Bi–In–Zn–Sb alloys 256
5.5.3 Reactions of solid cobalt with liquid Sn–Bi–In–Zn–Sb alloys 260
5.6 Peculiarities of kinetic dependences in solid-gas systems 272
5.6.1 Layer thickness-time relationships 272
5.6.2 Influence of evaporation on the growth rate of a chemical compound layer 276
5.6.3 Partial oxidation of chemical compounds 281
5.7 Reaction-diffusion kinetics in solid-liquid and solid-gas systems: short conclusions 285

CONCLUDING REMARKS 287

REFERENCES 291

KEYWORD INDEX 313